

## WE CLAIM:

- 1. A memory cell comprising:
- a substrate that comprises a first region and a second region with a channel therebetween and a gate above said channel;
  - a charge trapping region that contains a first amount of charge,
- a layer positioned between said channel and said charge trapping region, wherein said layer has a thickness such that said first amount of charge is prevented from directly tunneling into said layer; and
  - a silicided bitline.
- 2. The memory cell of claim 1, comprising an oxide that overlies said silicided bitline.
- 3. The memory cell of claim 1, comprising a polysilicon layer that overlies said gate.
- 4. The memory cell of claim 3, comprising a silicide layer that overlies said polysilicon layer.
- 5. The memory cell of claim 1, wherein said charge trapping region comprises silicon nitride.
- 6. The memory cell of claim 1, wherein said gate comprises an N-type material.
- 7. The memory cell of claim 6, wherein said gate comprises a polycrystalline silicon.
- 8. The memory cell of claim 1, further comprising an insulating layer formed on and overlaying said charge trapping region.

- 9. The memory cell of claim 8, wherein said insulating layer comprises silicon dioxide.
- 10. The memory cell of claim 9, wherein said charge trapping region comprises silicon nitride.
- 11. The memory cell of claim 1, wherein said memory cell comprises an EEPROM memory cell.
- 12. The memory cell of claim 1, wherein said memory cell comprises a two-bit memory cell.
- The memory cell of claim 1, wherein said substrate comprises a P-type substrate.
- 14. A process of fabricating a memory cell comprising a substrate that comprises a first region and a second region with a channel therebetween, the method comprising:

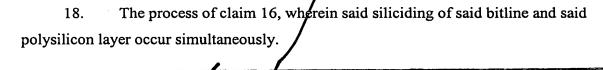
forming a gate above said channel of said substrate; forming a bitline; and

silic/ding said bitline.

- 15. The process of claim 14, comprising forming an oxide over said silicided bitline.
- 16. The process of claim 14, wherein prior to said forming a bitline a polysilicon layer is formed over said gate.

The process of claim 16, comprising siliciding said polysilicon layer.





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19. The process of claim 14, comprising:
forming a charge trapping region that contains a first amount of charge; and

forming a layer between said channel and said charge trapping region, wherein said layer has a thickness such that said first amount of charge is prevented from directly tunneling into said layer.

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20. The process of claim 19, wherein said charge trapping region comprises silicon nitride.

material.

21. The process of claim 14, wherein said gate comprises an N-type

silicon.

22. The process of claim 21, wherein said gate comprises a polycrystalline on.

- 23. The process of claim 19, further comprising forming an insulating layer on said charge trapping region.
- 24. The process of claim 23, wherein said insulating layer comprises silicon dioxide.
- 25. The process of claim 24, wherein said charge trapping region comprises silicon natride.

- 26. The process of claim 14, wherein said memory cell comprises an EEPROM memory cell.
- 27. The process of claim 14, wherein said memory cell comprises a two-bit memory cell.
- 28. The process of claim 14, wherein said substrate comprises a P-type substrate.
- 29. The process of claim 14, further comprising scaling the length of said bitline.

30. The process of claim 29, wherein said scaling comprises reducing the thermal cycle of said bitline.